

BYV34-600

Dual rectifier diode ultrafast

Rev. 01 — 4 October 2007

Product data sheet

1. Product profile

1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low switching loss
- Low thermal resistance
- Low forward voltage drop
- High thermal cycling performance

1.3 Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \leq 600 \text{ V}$
- $I_{O(AV)} \leq 20 \text{ A}$
- $V_F \leq 1.16 \text{ V}$
- $t_{rr} \leq 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	anode 1		
2	cathode		
3	anode 2		
mb	mounting base; cathode		

SOT78 (3-lead TO-220AB)

sym084

3. Ordering information

Table 2. Ordering information

Type number	Package		Version
	Name	Description	
BYV34-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; $\delta = 1.0$; $T_{mb} \leq 138\text{ °C}$	-	600	V
$I_{O(AV)}$	average output current	square waveform; $\delta = 0.5$; $T_{mb} \leq 107\text{ °C}$; both diodes conducting	-	20	A
I_{FRM}	repetitive peak forward current	$t = 25\text{ }\mu\text{s}$; square waveform; $\delta = 0.5$; $T_{mb} \leq 107\text{ °C}$; per diode	-	20	A
I_{FSM}	non-repetitive peak forward current	$t = 10\text{ ms}$; sinusoidal waveform; per diode	-	120	A
		$t = 8.3\text{ ms}$; sinusoidal waveform; per diode	-	132	A
T_{stg}	storage temperature		-40	+150	°C
T_j	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 1	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

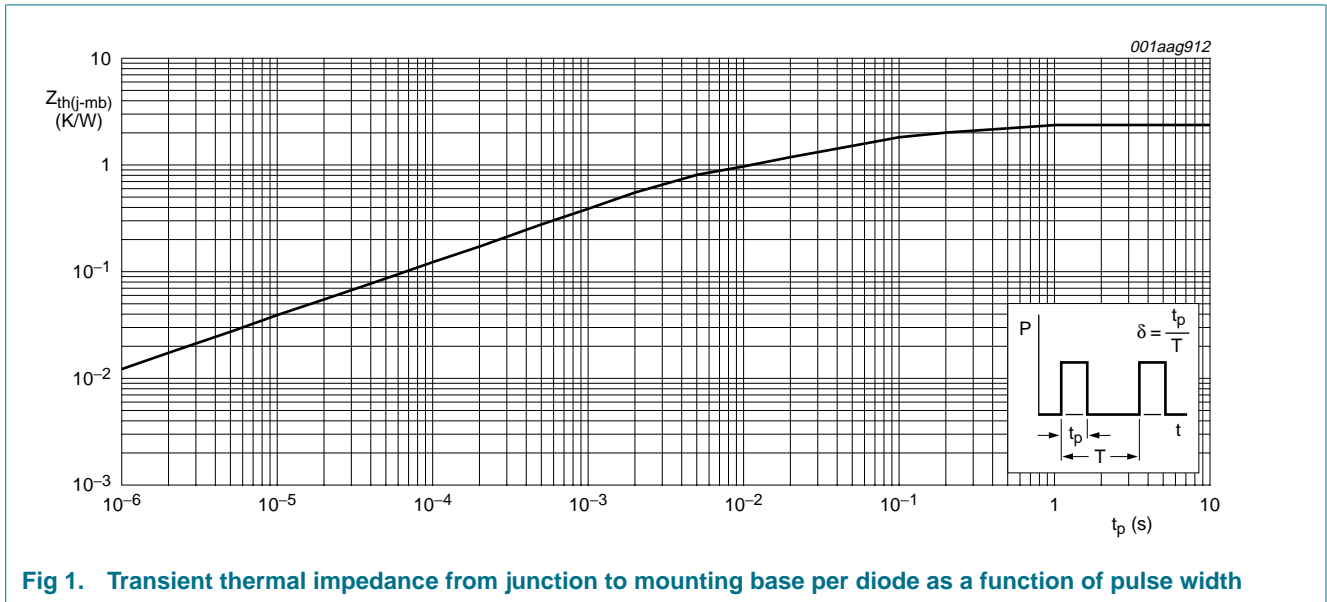


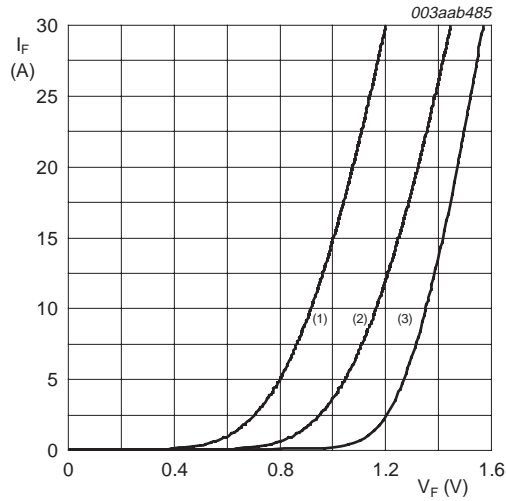
Fig 1. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

6. Characteristics

Table 5. Characteristics

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 10\text{ A}$; $T_j = 150\text{ }^\circ\text{C}$; see Figure 2	-	0.92	1.16	V
		$I_F = 20\text{ A}$; see Figure 2	-	1.07	1.48	V
I_R	reverse current	$V_R = 600\text{ V}$	-	10	50	μA
		$V_R = 600\text{ V}$; $T_j = 100\text{ }^\circ\text{C}$	-	0.2	0.6	mA
Dynamic characteristics						
Q_r	recovered charge	$I_F = 2\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 20\text{ A}/\mu\text{s}$; see Figure 3	-	40	70	nC
t_{rr}	reverse recovery time	$I_F = 1\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 100\text{ A}/\mu\text{s}$; see Figure 3	-	50	60	ns
I_{RM}	peak reverse recovery current	$I_F = 10\text{ A}$ to $V_R \geq 30\text{ V}$; $di_F/dt = 50\text{ A}/\mu\text{s}$; $T_j = 100\text{ }^\circ\text{C}$; see Figure 3	-	3	5	A
V_{FR}	forward recovery voltage	$I_F = 10\text{ A}$; $di_F/dt = 10\text{ A}/\mu\text{s}$; see Figure 4	-	3.2	-	V



- (1) $T_j = 150\text{ }^\circ\text{C}$; typical values
- (2) $T_j = 150\text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25\text{ }^\circ\text{C}$; maximum values

Fig 2. Forward current as a function of forward voltage

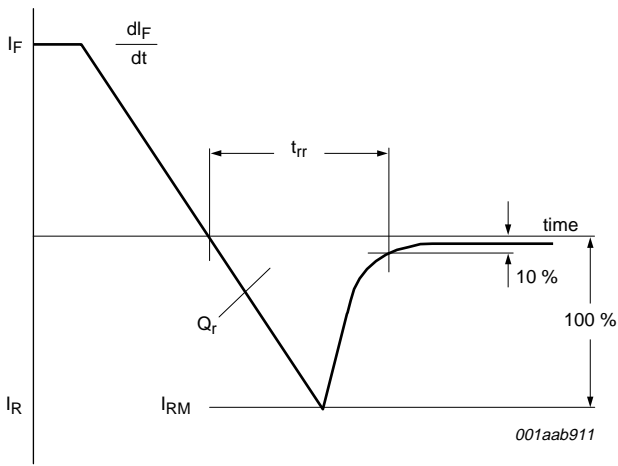


Fig 3. Reverse recovery definitions

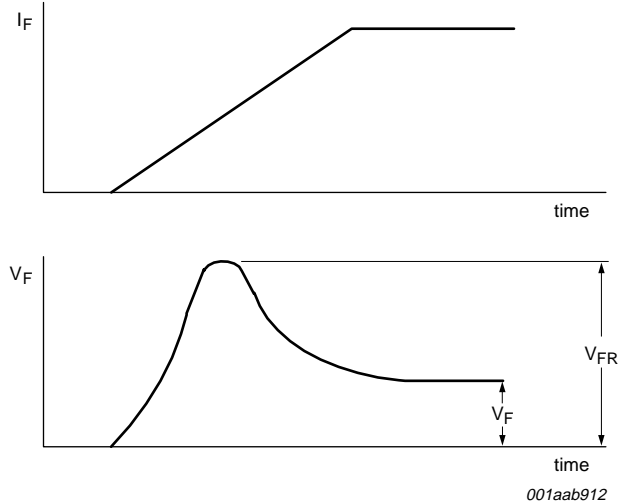
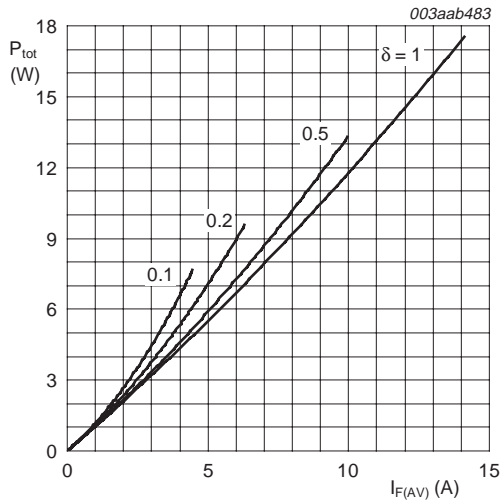
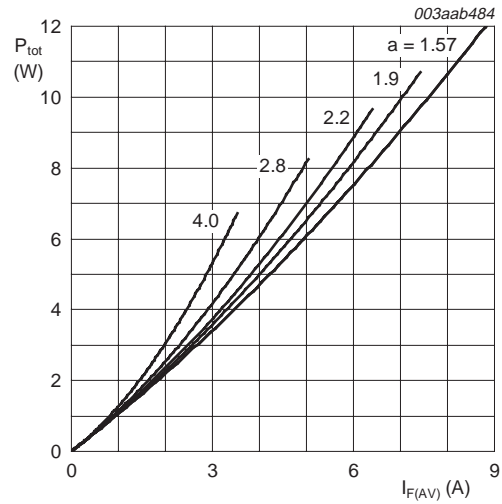


Fig 4. Forward recovery definitions



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

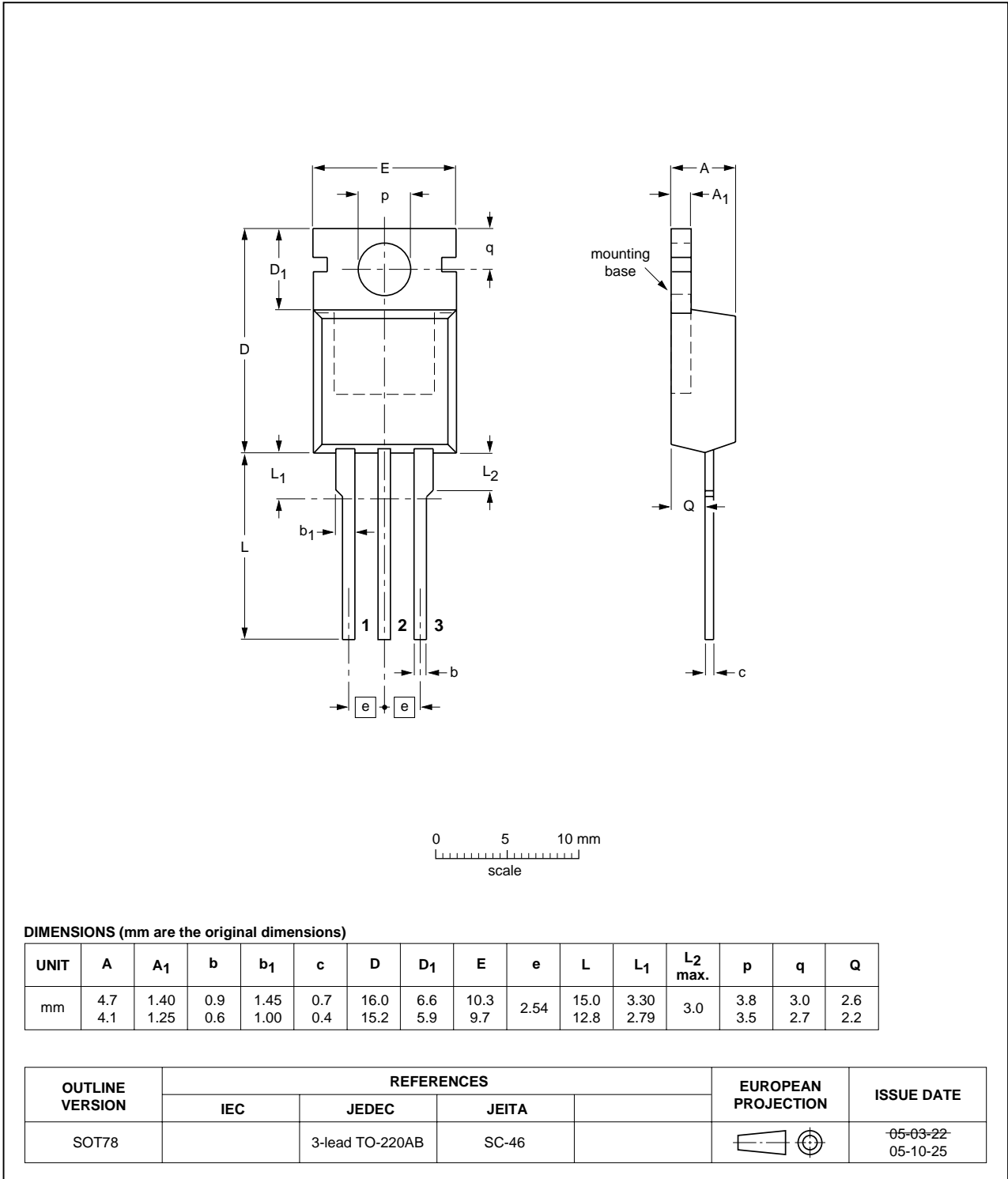


Fig 7. Package outline SOT78 (3-lead TO-220AB)

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV34-600_1	20071004	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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